1 Objective

This is the first lab dealing with the use of transistors in amplifiers. We will be dealing with the MOS common-source (CS) amplifier in this experiment. You will measure the transfer curve and from it, determine the bias point. The voltage gain and output resistance will be measured. From these measurements, you should understand the trade-offs involved in biasing a CS amplifier.

2 Prelab

1. Reading H&S: Chapter 8.1, 8.5
2. You will now consider biasing issues with FETs. Below is an NMOS transistor that will be configured as a common source amplifier. For the circuit in Fig. 1, determine the DC bias voltage $V_{IN}$ so that $V_{OUT} \approx 2.50$ V for $R_D = 5 \, \text{k}\Omega$. Use the following MOS parameters for hand calculation and for SPICE, in which you should plot $V_{OUT}$ vs. $V_{IN}$:
   - $V_{TO} = 0.9$ V, $K_p = 86 \times 10^{-6}$ A/V$^2$, $\lambda = 0.08 \, \text{V}^{-1}$
3. Derive the expressions for the small-signal parameters $g_m$ and $r_o$ using the drain current in saturation; evaluate these parameters at this bias point.
3 Static Measurements using HP 4155

3.1 Finding the Transfer Curve

The goal of this section is to bias the common-source amplifier in Fig. 2 properly. Using the HP/Agilent parameter analyzers, we can sweep $V_{IN}$ and see how the DC output voltage varies. In addition, we can use (EQ 1) to find how the magnitude of the small-signal gain ($G$) varies with the input bias voltage $V_{IN}$.

\[
G \approx \frac{\Delta V_{OUT}}{\Delta V_{IN}}
\]  

(EQ 1)

3.2 Circuit and Measurement Set Up

To make measurements of the output voltage, we need to use a VMU (voltage measurement unit), which functions as a voltmeter. Set up the circuit in Fig. 2 and make the appropriate parameter analyzer channel definitions. More specifically, use a SMU to sweep the voltage $v_{IN}$ from 0 V to 5 V (using a 5 mV step size or smaller), and observe the voltage $v_{OUT}$ using a VMU. Plot the output voltage $v_{OUT}$ versus $v_{IN}$, which is called the transfer curve.

Import the data points obtained into Excel, and use (EQ 1) to plot the small-signal gain versus $v_{OUT}$. Find the output voltage range for which the amplifier’s gain is greater than...
50% of the maximum gain. On what side of the maximum does the gain decrease sharply? Explain why.

**FIGURE 2.** Common Source Amplifier (Lab Chip 1)

3.3 Triode/Saturation Boundary

Determine the value of $V_{IN}$ at which the transistor enters the triode region; call this value $V_1$. Indicate this value on the two plots obtained in section 3.2 (i.e. the VTC and small-signal plots).

Recall that the test for a MOSFET to be in the saturation region is

$$V_{DS} \geq V_{GS} \angle V_{TN} = V_{DS(SAT)}$$

which implies that

$$V_{OUT} \geq V_{IN} \angle V_{TN} \quad (EQ \ 2)$$

What happens to the small-signal gain once the transistor enters the triode region?

3.4 Maximum Gain Bias Point

Find the input voltage $V_{IN}$ for maximum small-signal gain; call this value $V_2$. Are $V_1$ from section 3.3 and $V_2$ far apart? If we need to amplify a sinusoidal small-signal input voltage $v_{in}$ with an amplitude of 100 mV, can we bias this CS amplifier with $V_{IN} = V_2$? Hint: consider the range of the total input voltage $v_{IN} = V_{IN} + v_{in}(t)$.

3.5 Bias Point for 1 V Output Swing

Find a DC output bias point $V_{OUT}$ for which the small-signal voltage gain is greater than 2.5 and that allows an output swing of 1.6 V peak-to-peak, without severe distortion of
$v_{out}(t)$. The amplitude of the output voltage $v_{OUT}$’s time-varying component, in other words, could be as large as 800 mV.

### 3.6 Increased Drain Resistance

Now replace the drain resistor with $R_D = 100 \, \text{k}\Omega$ and repeat steps 3.2 - 3.5. How did the gain and the values of $V_1$ and $V_2$ change? Are the results consistent with the DC and small-signal models for this amplifier?

### 4 Common-Source Amplifier Two-Port Parameters

Figure 3 shows a common source amplifier. Let $R_D = 5 \, \text{k}\Omega$. Set your function generator such that it gives $V_{IN} + v_{in}(t)$. Use the input bias value $V_{IN}$ you found in 3.5 above.

#### 4.1 Small-signal voltage gain measurement

Let $v_{in}$ be a sinusoid with an amplitude of 100 mV at a frequency of 5 kHz. Use the oscilloscope to measure the the small-signal gain $v_{out} / v_{in}$. Compare the value you find to that which you determined in section 3.5.
4.2 Output resistance measurement

The output resistance $R_{\text{out}}$ can be measured using the standard approach described in Fig. 4. The technique uses the fact that the very large capacitor is an effective short circuit for sinusoidal signals at the measurement frequency, whereas it is an open circuit as far as the DC bias of the amplifier is concerned. This useful property of capacitors allows us to vary the load resistor ($R_{\text{VAR}}$) without altering the bias point of the transistor.

Measure the amplitude at $v_{\text{out}}$. Connect the capacitor and the variable resistor to the output of the circuit as depicted in Fig. 3. Adjust the resistance until the amplitude at $v_{\text{out}}$ is reduced by one-half. The value of the variable resistor is equal to the output resistance. Explain why this procedure finds the output resistance by applying the voltage form of the 2-port model of the common-source.

Compare your measurement to the predicted value of $R_{\text{out}}$ from the small-signal model; the channel-length modulation parameter is $\lambda = 0.08 \text{ V}^{-1}$ for this MOSFET. Calculate the DC drain current by using the bias point of $V_{\text{OUT}}$ and the measured value of $R_D$.

4.3 Clipping of the Output Voltage Waveform

Increase the amplitude of $v_{\text{in}}(t)$ until the output waveform $v_{\text{out}}(t)$ starts to become significantly distorted by “clipping.” What is the maximum amplitude of $v_{\text{out}}(t)$ before clipping is significant? Explain briefly the reason for clipping. Hint: consider why the lower portion of the waveform is distorted before the upper portion.

5 Optional Experiment

5.1 Modified drain resistance

Repeat section 4 with a drain resistance $R_D = 10 \text{ k}\Omega$. What are the differences between the measurements on the original amplifier and the one with the higher drain resistance?